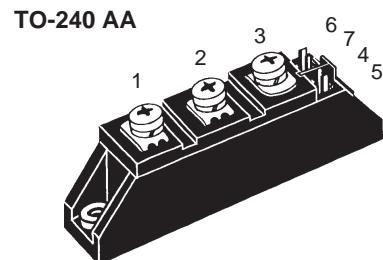


Thyristor Modules

Thyristor/Diode Modules

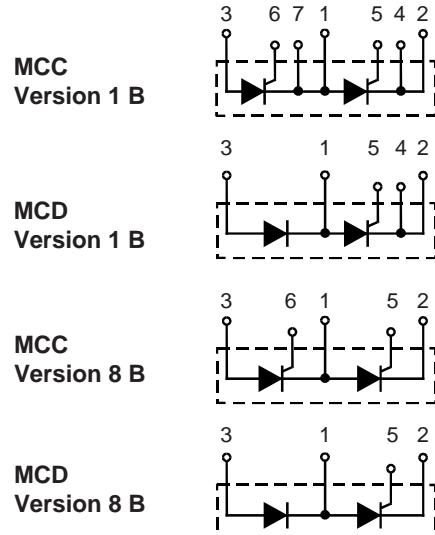
I_{TRMS} = 2x 180 A
I_{TAVM} = 2x 115 A
V_{RRM} = 800-1800 V

V _{RSM} V _{DSM}	V _{RRM} V _{DRM}	Type		
900	800	MCC 72-08io1 B	--	
1300	1200	MCC 72-12io1 B	MCD 72-12io1B	
1500	1400	MCC 72-14io1 B	--	
1700	1600	MCC 72-16io1 B	MCD 72-16io1B	
1900	1800	MCC 72-18io1 B	--	



Symbol	Test Conditions	Maximum Ratings		
I _{TRMS} , I _{FRMS}	T _{VJ} = T _{VJM}	180	A	
I _{TAVM} , I _{FAVM}	T _C = 63°C; 180° sine	115	A	
	T _C = 85°C; 180° sine	85	A	
I _{TSM} , I _{FSM}	T _{VJ} = 45°C; V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1700	A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1540	A
$\int i^2 dt$	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	14 450	A ² s
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	13 500	A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 µs V _D = 2/3 V _{DRM} I _G = 0.45 A di _G /dt = 0.45 A/µs	repetitive, I _T = 250 A non repetitive, I _T = I _{TAVM}	11 850	A ² s
			11 300	A ² s
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GR} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000	V/µs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30 µs t _p = 300 µs	10 5	W
P _{GAV}			0.5	W
V _{RGM}			10	V
T _{VJ}			-40...+125	°C
T _{VJM}			125	°C
T _{stg}			-40...+125	°C
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	3000 3600	V~
M _d	Mounting torque (M5) Terminal connection torque (M5)		2.5-4.0/22-35	Nm/lb.in.
Weight	Typical including screws		90	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.
 IXYS reserves the right to change limits, test conditions and dimensions



Features

- International standard package, JEDEC TO-240 AA
- Direct copper bonded Al₂O₃ -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 72873
- Gate-cathode twin pins for version 1B

Applications

- DC motor control
- Softstart AC motor controller
- Light, heat and temperature control

Advantages

- Space and weight savings
- Simple mounting with two screws
- Improved temperature and power cycling
- Reduced protection circuits

Symbol	Test Conditions	Characteristic Values		
I_{RRM}, I_{DRM}	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	5	mA	
V_T, V_F	$I_T, I_F = 300 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.74	V	
V_{TO}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85	V	
r_T		3.2	$\text{m}\Omega$	
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	2.5	V	
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	2.6	V	
		150	mA	
		200	mA	
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	0.2	V	
I_{GD}		10	mA	
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	450	mA	
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	200	mA	
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	2	μs	
t_q	$T_{VJ} = T_{VJM}; I_T = 150 \text{ A}, t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ typ. $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	185	μs	
Q_s	$T_{VJ} = T_{VJM}; I_T, I_F = 50 \text{ A}, -di/dt = 6 \text{ A}/\mu\text{s}$	170	μC	
I_{RM}		45	A	
R_{thJC}	per thyristor/diode; DC current	0.3	K/W	
	per module	0.15	K/W	
R_{thJK}	per thyristor/diode; DC current	0.5	K/W	
	per module	0.25	K/W	
d_s	Creepage distance on surface	12.7	mm	
d_A	Strike distance through air	9.6	mm	
a	Maximum allowable acceleration	50	m/s^2	

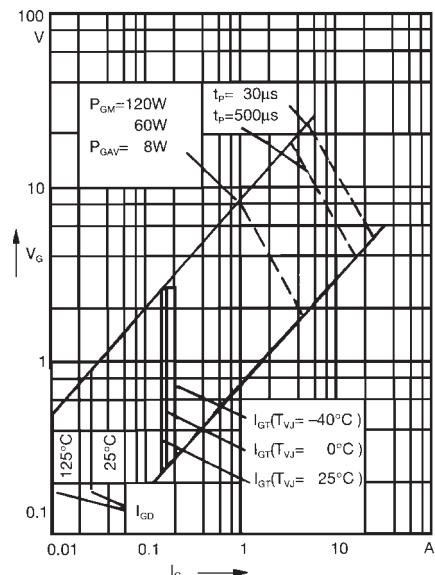


Fig. 1 Gate trigger characteristics

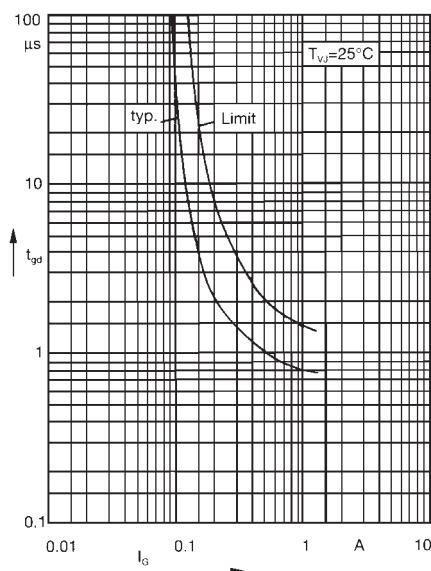
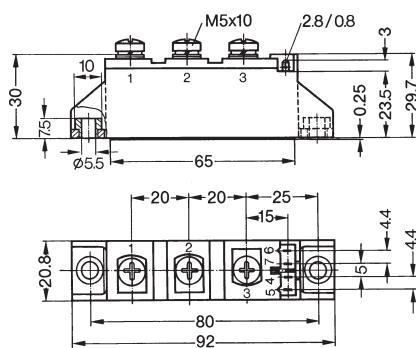


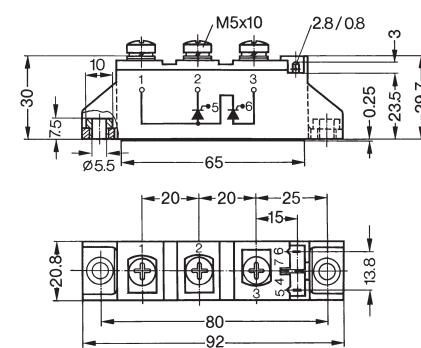
Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm ≈ 0.0394")

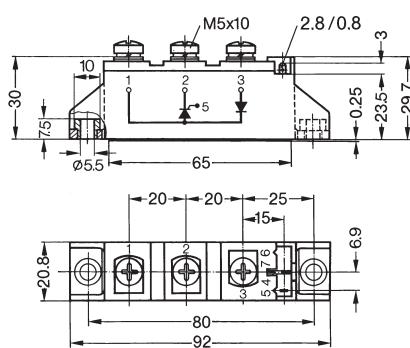
MCC / MCD Version 1 B



MCC Version 8 B



MCD Version 8 B



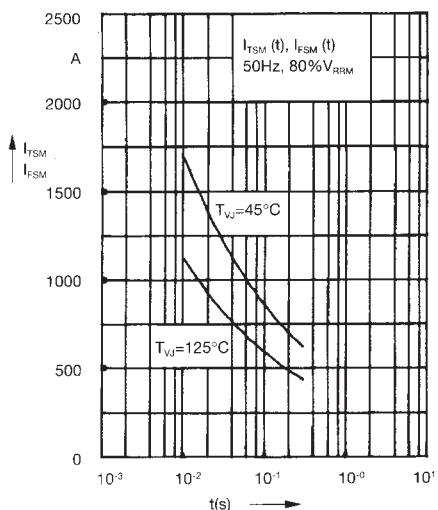


Fig. 3 Surge overload current
 I_{TSM}, I_{FSM} : Crest value, t: duration

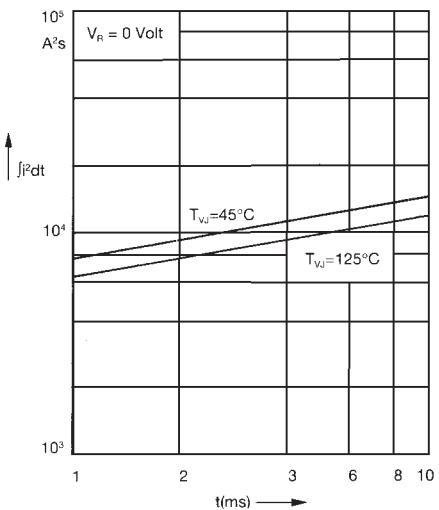


Fig. 4 $\int j^2 dt$ versus time (1-10 ms)

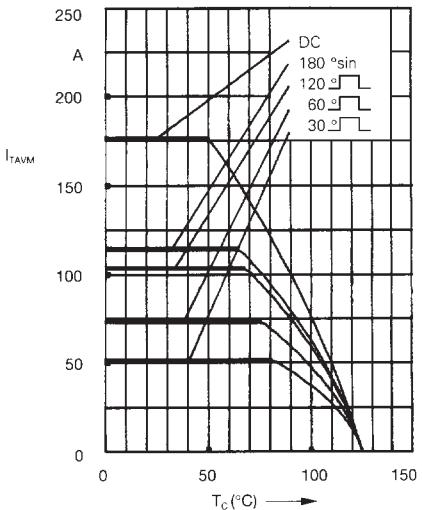


Fig. 4a Maximum forward current at case temperature

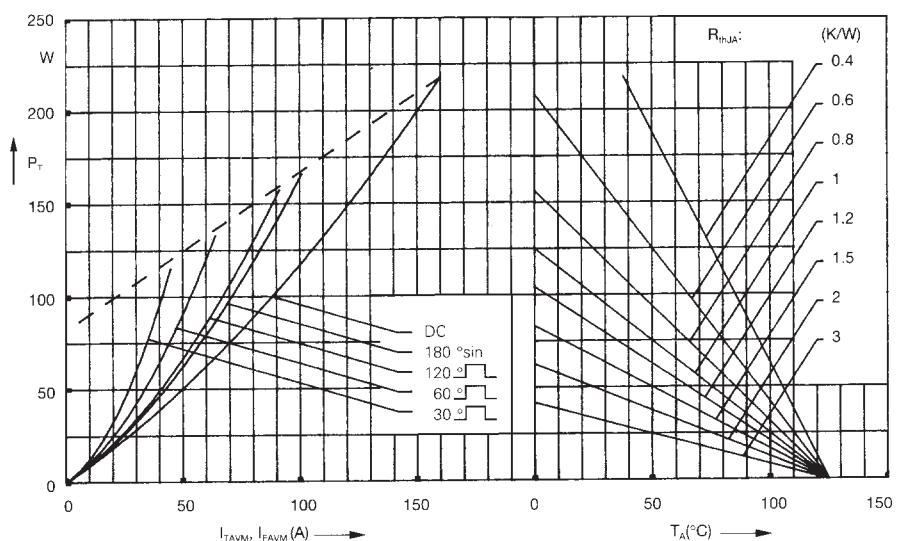


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

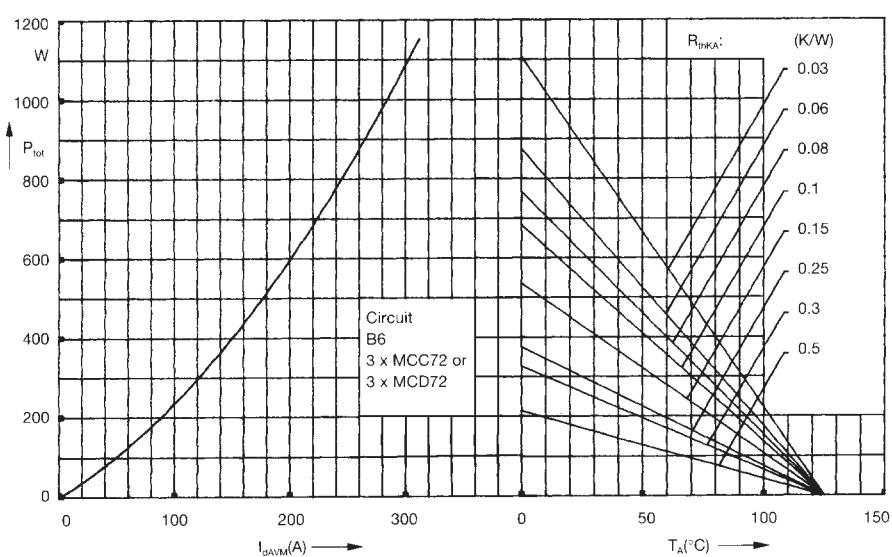


Fig. 6 Three phase rectifier bridge:
Power dissipation versus direct output current and ambient temperature

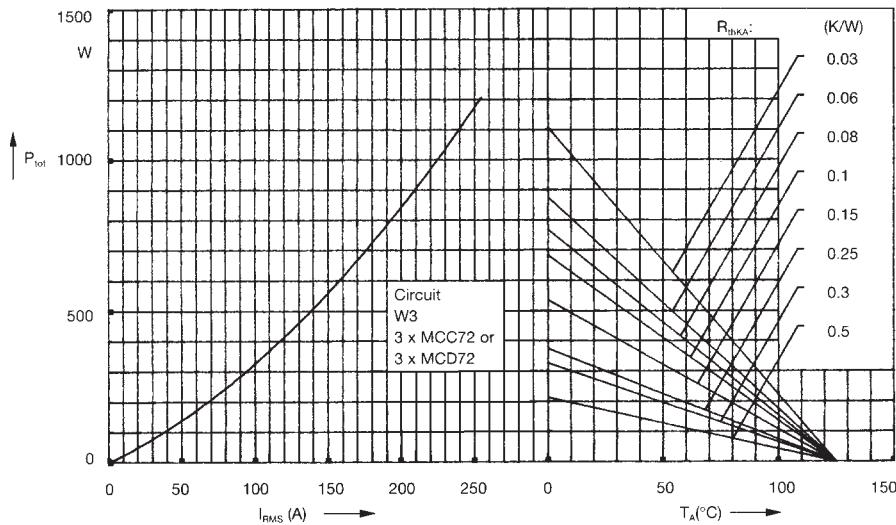


Fig. 7 Three phase AC-controller:
Power dissipation versus RMS
output current and ambient
temperature

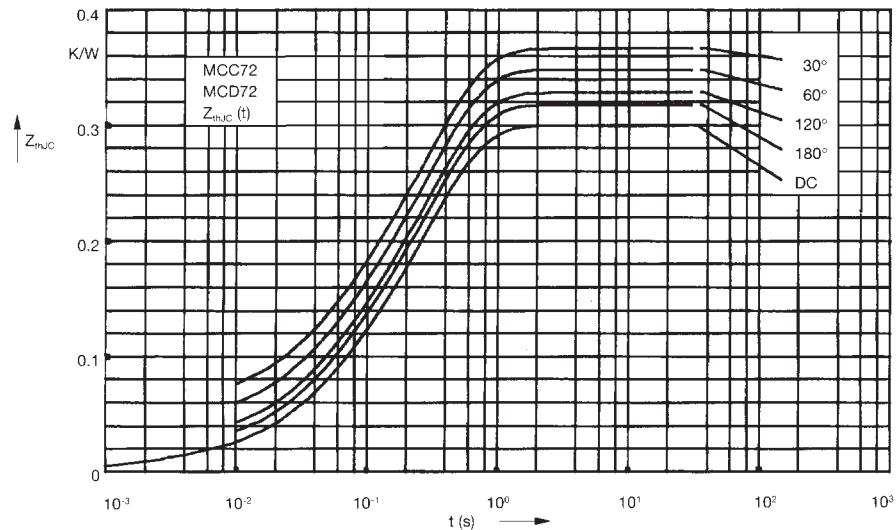


Fig. 8 Transient thermal impedance
junction to case (per thyristor or
diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.3
180°	0.31
120°	0.33
60°	0.35
30°	0.37

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.008	0.0019
2	0.054	0.047
3	0.238	0.3

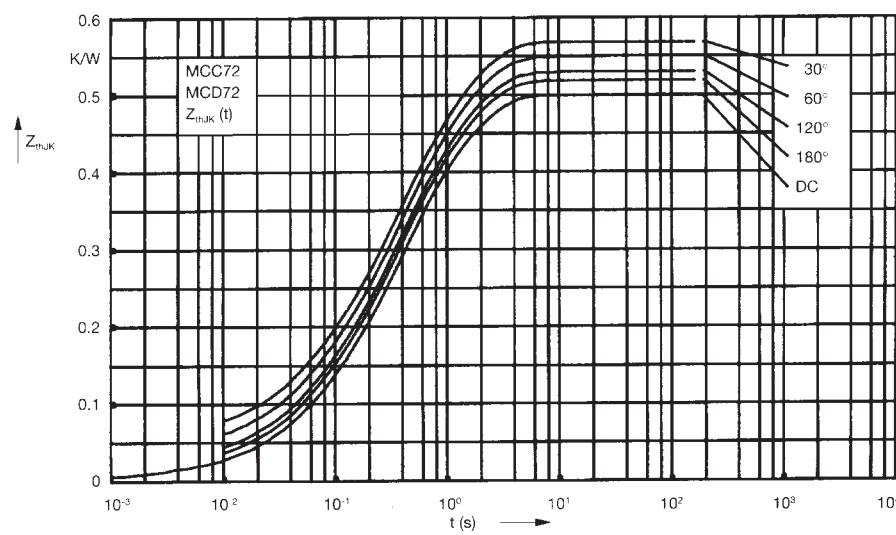


Fig. 9 Transient thermal impedance
junction to heatsink (per thyristor or
diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.5
180°	0.51
120°	0.53
60°	0.55
30°	0.57

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.008	0.0019
2	0.054	0.047
3	0.238	0.3
4	0.2	1.25